

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No. . . . . Unknown  
 Filing Date . . . . . December 4, 2000  
 Inventor . . . . . Charles H. Dennison  
 Assignee . . . . . Micron Technology, Inc.  
 Group / Unit . . . . . Unknown  
 Examiner . . . . . Unknown  
 Attorney Pocket No. . . . . MI22-1577  
 Title: Field Effect Transistors, Integrated Circuitry, Methods of Forming Field  
 Effect Transistor Gates, and Methods of Forming Integrated Circuitry

**PRELIMINARY AMENDMENT**

**To:** Box Patent Application  
 Assistant Commissioner for Patents  
 Washington, D.C. 20231  
  
**From:** Mark S. Matkin (Tel. 509-624-4276; Fax 509-838-3424)  
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I hereby enter the following amendments prior to examining the above-  
 identified application.

**AMENDMENTS****In the Specification**

Before the "Technical Field" section, please insert the following:

**--RELATED PATENT DATA**

This patent resulted from a continuation application of U.S. Patent  
 Application Serial No. 09/138,150, filed August 21, 2000, entitled "Field Effect

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